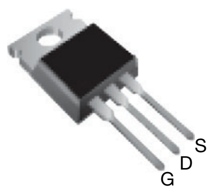
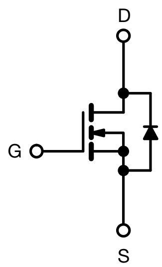
Power MOSFET

TO-220AB





N-Channel MOSFET

PRODUCT SUMMARY		
V_{DS} (V)	500	
$R_{DS(on)}$ (Ω)	V_{GS} = 10 V	0.85
Q_g max. (nC)	38	
Q_{gs} (nC)	9.0	
Q_{gd} (nC)	18	
Configuration	Single	

FEATURES

- Low gate charge Q_g results in simple drive requirement
- Improved gate, avalanche, and dynamic dV/dt ruggedness
- Fully characterized capacitance and avalanche voltage and current
- Effective C_{oss} specified
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

Pb Available
RoHS* Available

Note

* This datasheet provides information about parts that are RoHS-compliant and / or parts that are non RoHS-compliant. For example, parts with lead (Pb) terminations are not RoHS-compliant. Please see the information / tables in this datasheet for details

APPLICATIONS

- Switch mode power supply (SMPS)
- Uninterruptable power supply
- High speed power switching

TYPICAL SMPS TOPOLOGIES

- Two transistor forward
- Half bridge
- Full bridge

ORDERING INFORMATION	
Package	TO-220AB
Lead (Pb)-free	IRF840APbF
Lead (Pb)-free and halogen-free	IRF840APbF-BE3

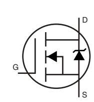
ABSOLUTE MAXIMUM RATINGS (T_C = 25 °C, unless otherwise noted)

PARAMETER			SYMBOL	LIMIT	UNIT
Drain-source voltage			V_{DS}	500	V
Gate-source voltage			V_{GS}	± 30	
Continuous drain current	V_{GS} at 10 V	T_C = 25 °C	I_D	8.0	A
		T_C = 100 °C		5.1	
Pulsed drain current [a]			I_{DM}	32	
Linear derating factor				1.0	W/°C
Single pulse avalanche energy [b]			E_{AS}	510	mJ
Repetitive avalanche current [a]			I_{AR}	8.0	A
Repetitive avalanche energy [a]			E_{AR}	13	mJ
Maximum power dissipation	T_C = 25 °C		P_D	125	W
Peak diode recovery dV/dt [c]			dV/dt	5.0	V/ns
Operating junction and storage temperature range			T_J, T_{stg}	-55 to +150	°C
Soldering recommendations (peak temperature) [d]	For 10 s			300	
Mounting torque	6-32 or M3 screw			10	lbf · in
				1.1	N · m

Notes

a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)
b. V_{DD} = 50 V, starting T_J = 25 °C, L = 16 mH, R_g = 25 Ω, I_{AS} = 8.0 A (see fig. 12)
c. $I_{SD} \leq$ 8.0 A, dI/dt $\leq$ 100 A/μs, $V_{DD} \leq V_{DS}$, $T_J \leq$ 150 °C
d. 1.6 mm from case

THERMAL RESISTANCE RATINGS				
PARAMETER	**SYMBOL**	**TYP.**	**MAX.**	**UNIT**
Maximum junction-to-ambient	R_{thJA}	-	62	°C/W
Case-to-sink, flat, greased surface	R_{thCS}	0.50	-	
Maximum junction-to-case (drain)	R_{thJC}	-	1.0	

SPECIFICATIONS (T_J = 25 °C, unless otherwise noted)						
PARAMETER	**SYMBOL**	**TEST CONDITIONS**	**MIN.**	**TYP.**	**MAX.**	**UNIT**
Static						
Drain-source breakdown voltage	V_{DS}	V_{GS} = 0 V, I_D = 250 μA	500	-	-	V
V_{DS} temperature coefficient	$\Delta V_{DS}/T_J$	Reference to 25 °C, I_D = 1 mA	-	0.58	-	V/°C
Gate-source threshold voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 μA	2.0	-	4.0	V
Gate-source leakage	I_{GSS}	V_{GS} = ± 30 V	-	-	± 100	nA
Zero gate voltage drain current	I_{DSS}	V_{DS} = 500 V, V_{GS} = 0 V	-	-	25	μA
		V_{DS} = 400 V, V_{GS} = 0 V, T_J = 125 °C	-	-	250	
Drain-source on-state resistance	$R_{DS(on)}$	V_{GS} = 10 V; I_D = 4.8 A [b]	-	-	0.85	Ω
Forward transconductance	g_{fs}	V_{DS} = 50 V, I_D = 4.8 A [b]	3.7	-	-	S
Dynamic						
Input capacitance	C_{iss}	V_{GS} = 0 V, V_{DS} = 25 V, f = 1.0 MHz, see fig. 5	-	1018	-	pF
Output capacitance	C_{oss}		-	155	-	
Reverse transfer capacitance	C_{rss}		-	8.0	-	
Output capacitance	C_{oss}	V_{GS} = 0 V; V_{DS} = 1.0 V, f = 1.0 MHz		1490		
Output capacitance	C_{oss}	V_{GS} = 0 V; V_{DS} = 400 V, f = 1.0 MHz		42		
Effective output capacitance	C_{oss} eff.	V_{GS} = 0 V; V_{DS} = 0 V to 400 V [c]		56		
Total gate charge	Q_g	V_{GS} = 10 V; I_D = 8 A, V_{DS} = 400 V, see fig. 6 and 13 [b]	-	-	38	nC
Gate-source charge	Q_{gs}		-	-	9.0	
Gate-drain charge	Q_{gd}		-	-	18	
Turn-on delay time	$t_{d(on)}$	V_{DD} = 250 V, I_D = 8 A, R_g = 9.1 Ω, R_D = 31 Ω, see fig. 10 [b]	-	11	-	ns
Rise time	t_r		-	23	-	
Turn-off delay time	$t_{d(off)}$		-	26	-	
Fall time	t_f		-	19	-	
Gate input resistance	R_g	f = 1 MHz, open drain	0.7	-	3.7	Ω
Drain-Source Body Diode Characteristics						
Continuous source-drain diode current	I_S	MOSFET symbol showing the integral reverse p - n junction diode 	-	-	8.0	A
Pulsed diode forward current [a]	I_{SM}		-	-	32	
Body diode voltage	V_{SD}	T_J = 25 °C, I_S = 8 A, V_{GS} = 0 V [b]	-	-	2.0	V
Body diode reverse recovery time	t_{rr}	T_J = 25 °C, I_F = 8 A, dI/dt = 100 A/μs [b]	-	422	633	ns
Body diode reverse recovery charge	Q_{rr}		-	2.16	3.24	μC
Forward turn-on time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by L_S and L_D)				

Notes

a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)

b. Pulse width ≤ 300 μs; duty cycle ≤ 2 %

c. C_{oss} eff. is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DS}

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

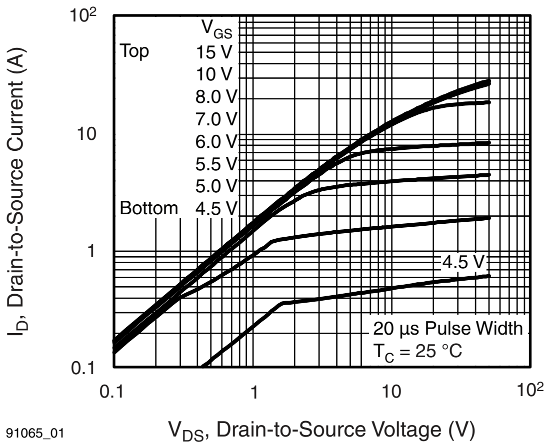


Fig. 1 - Typical Output Characteristics, T_C = 25 °C

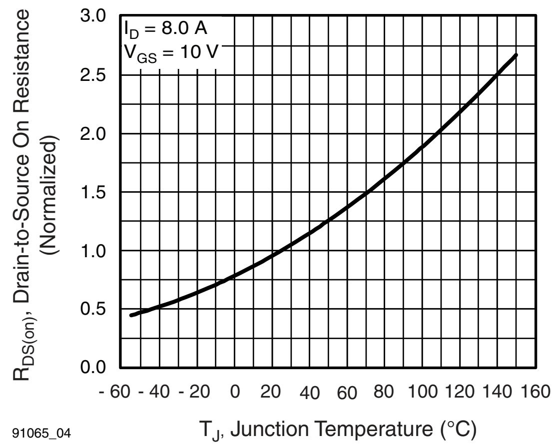


Fig. 4 - Normalized On-Resistance vs. Temperature

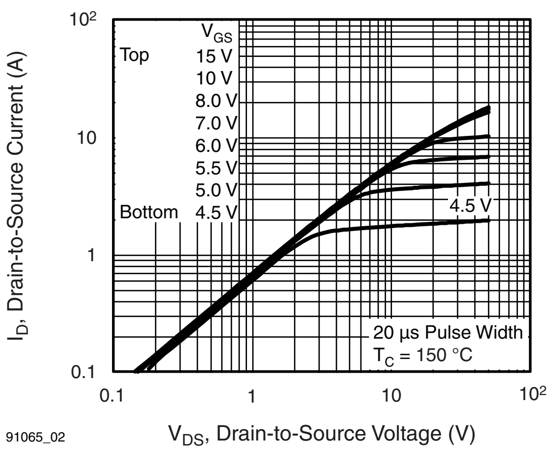


Fig. 2 - Typical Output Characteristics, T_C = 150 °C

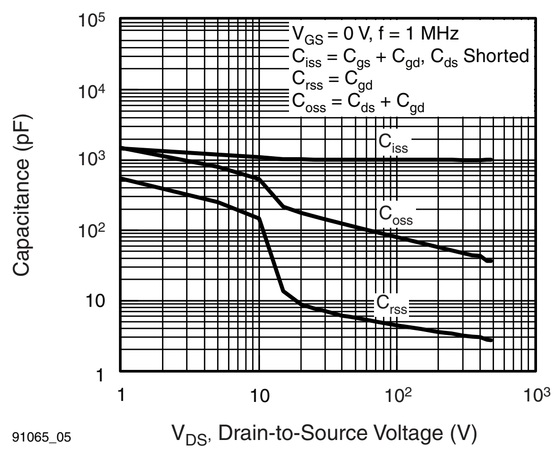


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

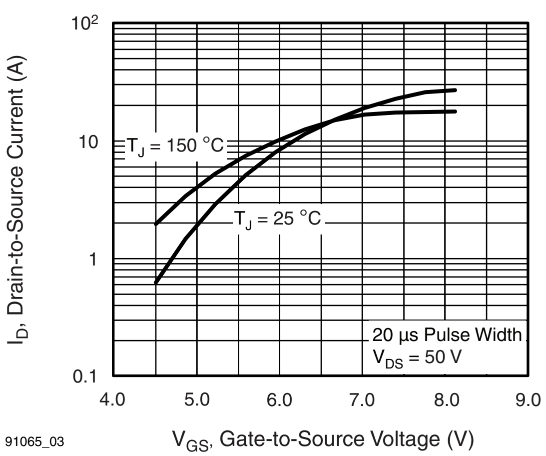


Fig. 3 - Typical Transfer Characteristics

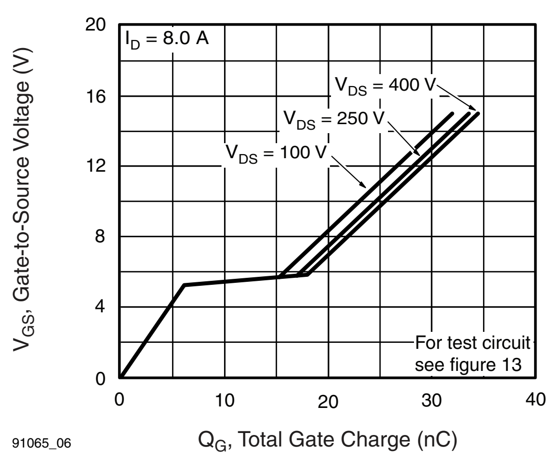


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

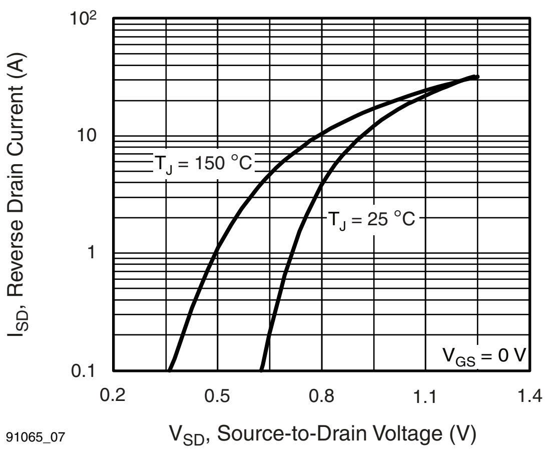


Fig. 7 - Typical Source-Drain Diode Forward Voltage

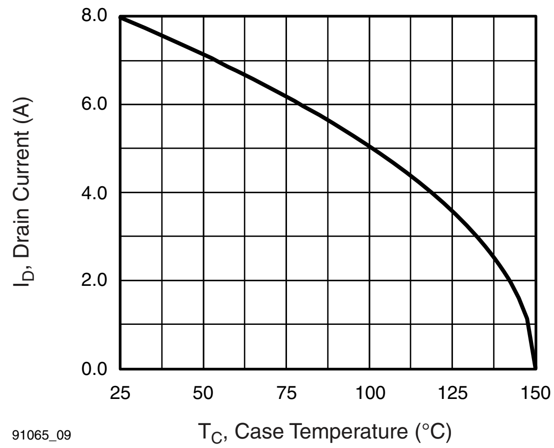


Fig. 9 - Maximum Drain Current vs. Case Temperature

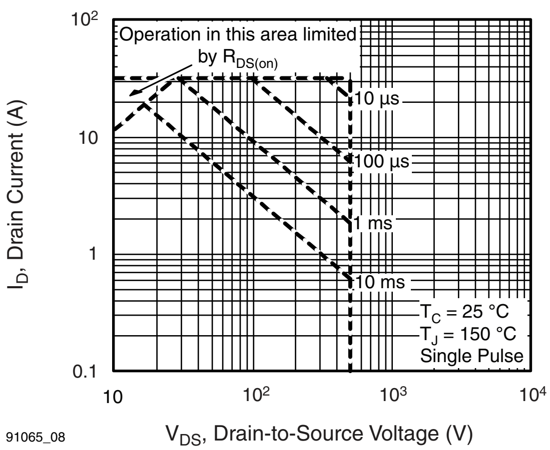


Fig. 8 - Maximum Safe Operating Area

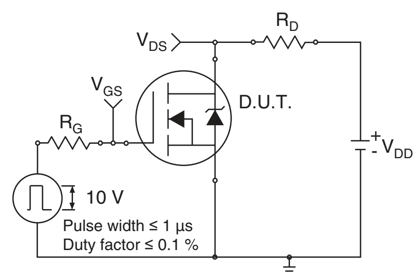


Fig. 10a - Switching Time Test Circuit

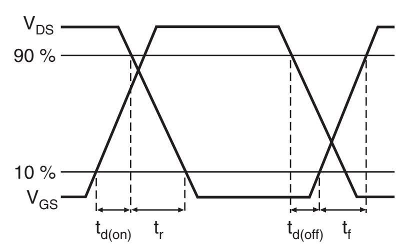


Fig. 10b - Switching Time Waveforms

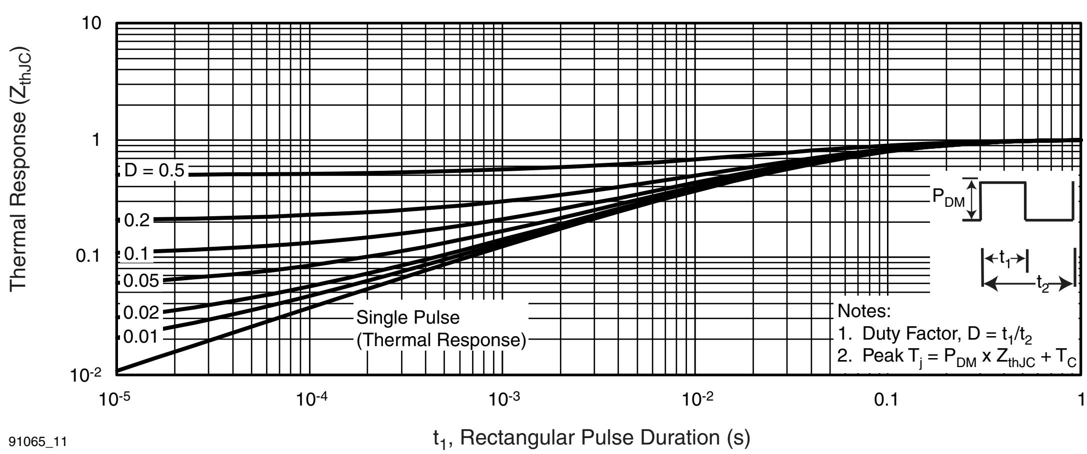


Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

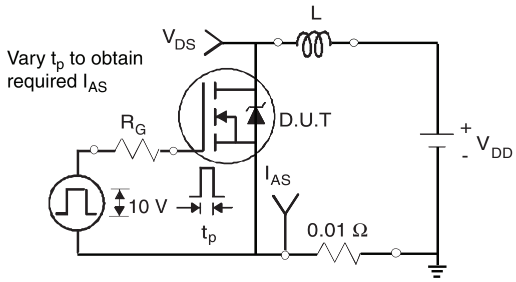


Fig. 12a - Unclamped Inductive Test Circuit

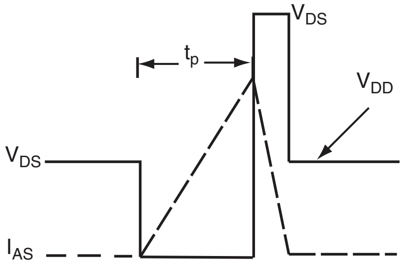


Fig. 12b - Unclamped Inductive Waveforms

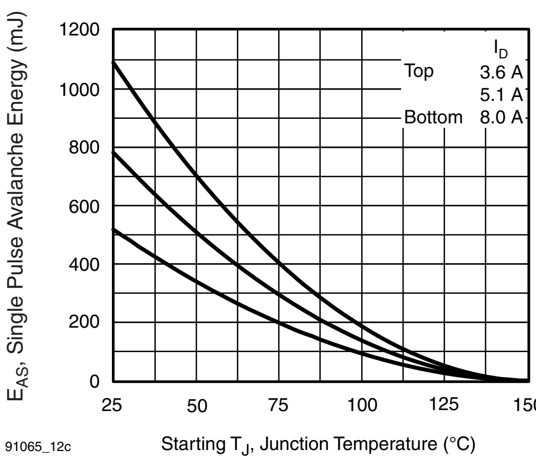


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

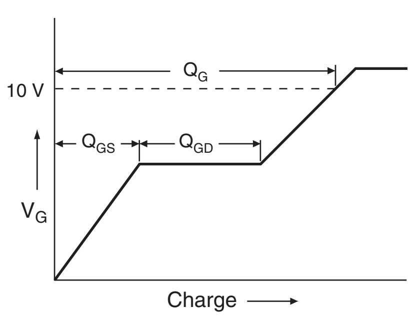


Fig. 12d - Basic Gate Charge Waveform

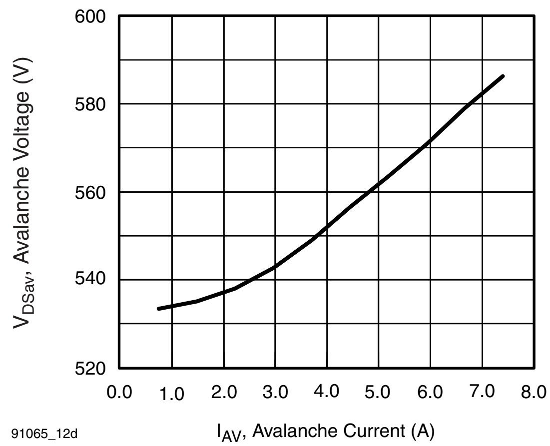


Fig. 13a - Typical Drain-to-Source Voltage vs. Avalanche Current

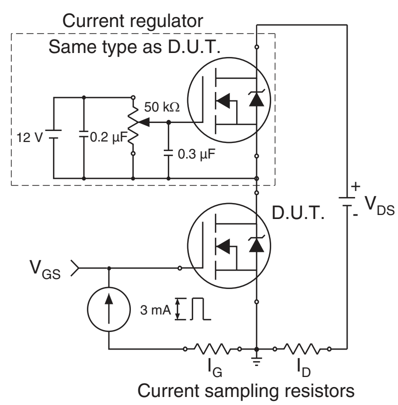
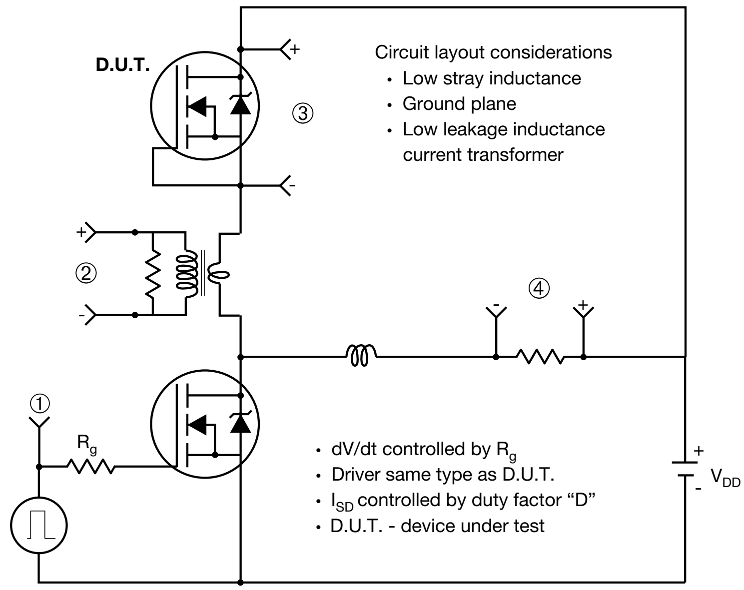
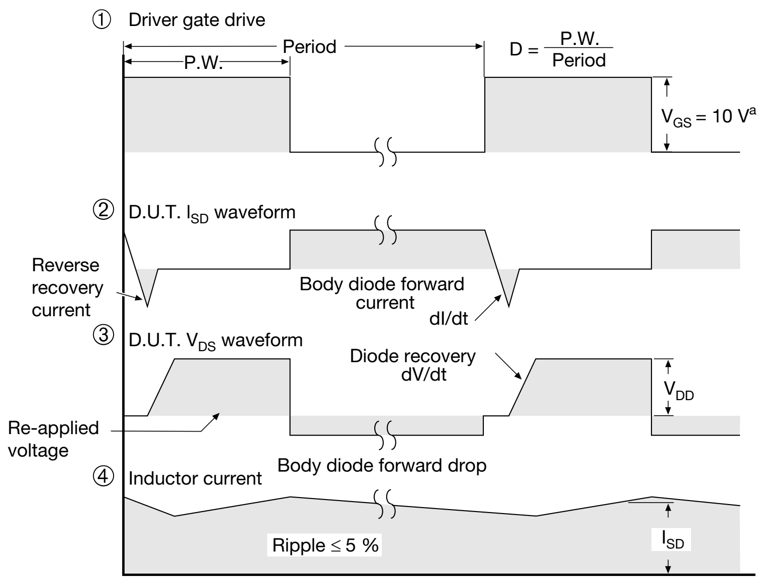


Fig. 13b - Gate Charge Test Circuit

Peak Diode Recovery dV/dt Test Circuit





Note

a. V_{GS} = 5 V for logic level devices

Fig. 14 - For N-Channel

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